

SILICON PNP TRANSISTOR EPITAXIAL PLANAR TYPE (PCT PROCESS)

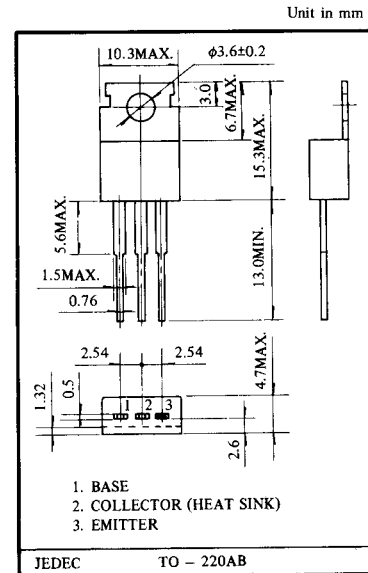
2SA 1276

APPLICATIONS

- Power Amplifier Applications.
- Car Radio And Car Stereo Output Stage Applications

FEATURES

- Good Linearity of h_{FE} .
- Complementary to 2SC 3230 and 5 Watts Output Applications.



MAXIMUM RATINGS (Ta = 25 °C)

CHARACTERISTIC	SYMBOL	RATING	UNIT	CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V_{CBO}	-30	V	Emitter Current	I_E	3	A
Collector-Emitter Voltage	V_{CEO}	-30	V	Collector Power Dissipation (Tc=25 °C)	P_C	10	W
Emitter-Base Voltage	V_{EBO}	-5	V	Junction Temperature	T_j	150	°C
Collector Current	I_C	-3	A	Storage Temperature Range	Tstg	-55 ~ 150	°C

ELECTRICAL CHARACTERISTICS (Ta = 25 °C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	I_{CBO}	$V_{CB} = -20V, I_E = 0$	-	-	-1.0	μA
Emitter Cut-off Current	I_{EBO}	$V_{EB} = -5V, I_C = 0$	-	-	-1.0	μA
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C = -10mA, I_B = 0$	-30	-	-	V
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	$I_E = -1mA, I_C = 0$	-5	-	-	V
DC Current Gain	$h_{FE(1)}$ (Note)	$V_{CE} = -2V, I_C = -0.5A$	70	-	240	
	$h_{FE(2)}$	$V_{CE} = -2V, I_C = -2.5A$	25	-	-	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = -2A, I_B = -0.2A$	-	-0.3	-0.8	V
Base-Emitter Voltage	V_{BE}	$V_{CE} = -2V, I_C = -0.5A$	-	-0.75	-1.0	V
Transition Frequency	f_T	$V_{CE} = -2V, I_C = -0.5A$	-	100	-	MHz
Collector Output Capacitance	C_{ob}	$V_{CB} = -10V, I_E = 0, f = 1MHz$	-	40	-	pF

NOTE: According to $h_{FE(1)}$ Classified as follows.

0	70 - 140	Y	120 - 240
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